



F. Silicon and Group-IV Devices and Integration Technology **분과**

2019년 2월 14일(목), 09:00-10:30

Room C (가람홀, 2층)

[TC1-F] Advanced Integration Technology and Photonics

좌장: 김춘환 상무(SK하이닉스), 정성웅 연구위원(SK하이닉스)

<p>TC1-F-1 09:00-09:30</p>	<p>[초청] Silicon Photonics Lasers and Photodetectors for Communications and Sensing Il-Sug Chung <i>School of Electrical and Computer Engineering, UNIST</i></p>
<p>TC1-F-2 09:30-09:45</p>	<p>Effective Work Function Modulation Using Dipole Mechanism with Al₂O₃ on HfO₂ Atomic Layer Deposition Munhyeon Kim^{1,2}, Sihyun Kim¹, Kitae Lee¹, Soyoun Kim¹, Junil Lee¹, Hyun-Min Kim¹, Ryoongbin Lee¹, Sangwan Kim³, and Byung-Gook Park¹ ¹<i>Department of Electrical and Computer Engineering, Seoul National University,</i> ²<i>Samsung Electronics Semiconductor R&D Center,</i> ³<i>Department of Electrical and Computer Engineering, Ajou University</i></p>
<p>TC1-F-3 09:45-10:00</p>	<p>The Lowest On-Resistance and Robust 0.13μm BCD Technology Implementation Utilizing HTO Field Plate for Mobile Market Kuemju Lee, Daehoon Kim, Jaeek Kim, Junghun Choi, Jaehee Lee, and Inwook Cho ¹<i>Technology Development office, SK Hynix</i></p>
<p>TC1-F-4 10:00-10:15</p>	<p>Reduction of Contact Resistance between NiSi and n/p-Si Using Ho Interlayer Sunil Babu Eadi¹, Jeong Chan Lee¹, Jungwoo Oh², and Hi-Deok Lee¹ ¹<i>Department of Electronic Engineering, Chungnam National University,</i> ²<i>School of Integrated Technology, Yonsei Institute of Convergence Technology, Yonsei University</i></p>
<p>TC1-F-5 10:15-10:30</p>	<p>Low-Temperature Hybrid Dopant Activation Technique Using Pulsed Green Laser for Heavily-Doped n-Type SiGe Source/Drain Seung-Geun Kim¹, Gwang-Sik Kim², Seung-Hwan Kim², June Park³, and Hyun-Yong Yu² ¹<i>Department of Semiconductor Systems Engineering, Korea University,</i> ²<i>School of Electrical Engineering, Korea University,</i> ³<i>Department of Nano Semiconductor Engineering, Korea University</i></p>